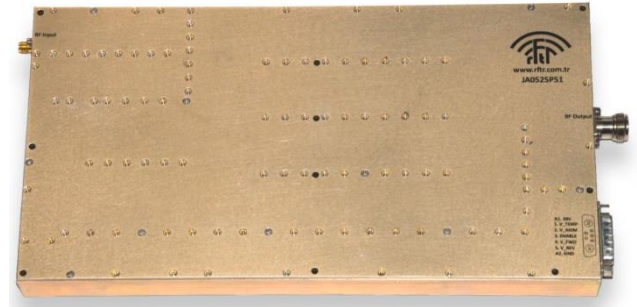


JA0530P52; 500 MHz – 3000 MHz 160W

- Solid-state Class AB design
- GaN on SiC Transistors
- High reliability and ruggedness
- Ultra Broadband
- Temperature and Current Monitorings

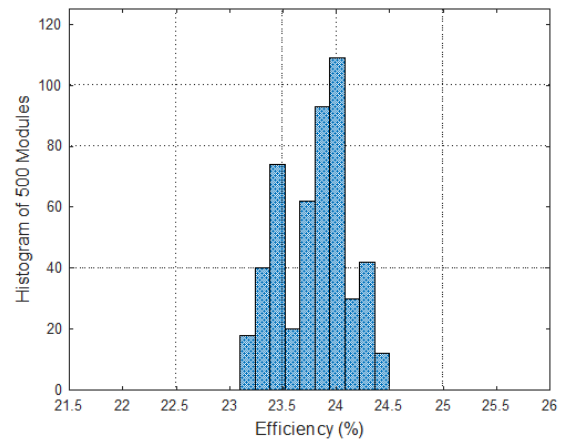


ELECTRICAL & ENVIRONMENTAL SPECIFICATIONS

Frequency:	500-3000 MHz (Can be extended to 400 MHz)
Output Power:	160 W min. CW
Nominal Gain:	52 dB
Gain Flatness:	± 2.5 dB
Input VSWR:	2:1 max.
Load VSWR for Survival:	∞:1 for 1min.
DC Supply Voltage:	36 V
DC Current:	17.5 A Avg
Operating Case Temp.:	-40 °C to 85 °C
Storage Temperature:	-40 °C to 85 °C
Shock:	MIL-STD-810F, 516.5
Vibration:	MIL-STD-810F, 514.5

INTERFACES

RF Input:	SMA Female
RF Output:	N Female
7W2 DSUB:	A1) 36 V A2) GND 1) Temperature 2) Current 3,4,5) NC



MECHANICAL SPECIFICATIONS

Size (mm) :	300 x 156 x 28
(inch) :	11.8 x 6.15 x 1.1
Weight :	2200 gr.
Plating :	Yellow Chromate

